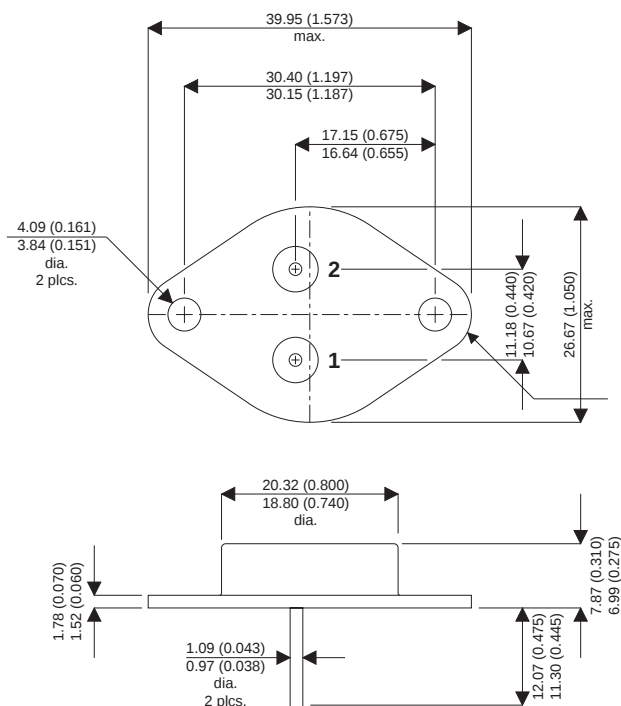


MECHANICAL DATA

Dimensions in mm (inches)


TO-3 Metal Package

Pin 1 – Gate

Pin 2 – Source

Case – Drain

**P-CHANNEL
POWER MOSFET**
 V_{DSS} **–200V**
 $I_{D(cont)}$ **–6.5A**
 $R_{DS(on)}$ **0.8 Ω**
FEATURES

- HERMETICALLY SEALED TO-3 METAL PACKAGE
- SIMPLE DRIVE REQUIREMENTS
- SCREENING OPTIONS AVAILABLE

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	$\pm 20V$
I_D	Continuous Drain Current ($V_{GS} = 0$, $T_{case} = 25^{\circ}C$)	–6.5A
I_D	Continuous Drain Current ($V_{GS} = 0$, $T_{case} = 100^{\circ}C$)	–4A
I_{DM}	Pulsed Drain Current ¹	–28A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	75W
	Linear Derating Factor	0.6W/ $^{\circ}C$
E_{AS}	Single Pulse Avalanche Energy ²	66mJ
I_{AR}	Avalanche Current ²	–6.5A
E_{AR}	Repetitive Avalanche Energy ²	7.5mJ
dv/dt	Peak Diode Recovery ³	–5V/ns
T_J , T_{stg}	Operating and Storage Temperature Range	–55 to +150 $^{\circ}C$
T_L	Lead Temperature 1.6mm (0.63”) from case for 10 sec.	300 $^{\circ}C$

Notes

1) Pulse Test: Pulse Width $\leq 300\mu s$, $\delta \leq 2\%$

2) @ $V_{DD} = -50V$, $L \geq 2.3mH$, $R_G = 25\Omega$, Peak $I_L = -6.5A$, Starting $T_J = 25^{\circ}C$

3) @ $I_{SD} \leq -6.5A$, $di/dt \leq -100A/\mu s$, $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^{\circ}C$, Suggested $R_G = 7.5\Omega$

ELECTRICAL CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter		Test Conditions		Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS							
BV _{DSS}	Drain – Source Breakdown Voltage	V _{GS} = 0	I _D = –1mA	–200			V
ΔBV _{DSS}	Temperature Coefficient of Breakdown Voltage	Reference to 25°C I _D = –1mA			–0.2		V/°C
R _{DS(on)}	Static Drain – Source On–State Resistance ¹	V _{GS} = 10V	I _D = –4A			0.80	Ω
		V _{GS} = 10V	I _D = –6.5A			0.92	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS}	I _D = –250mA	–2		–4	V
g _{fs}	Forward Transconductance ¹	V _{DS} ≥ –15V	I _{DS} = –4A	2			S (V)
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0	V _{DS} = 0.8BV _{DSS}			–25	μA
			T _J = 125°C			–250	
I _{GSS}	Forward Gate – Source Leakage	V _{GS} = –20V				–100	nA
I _{GSS}	Reverse Gate – Source Leakage	V _{GS} = 20V				100	
DYNAMIC CHARACTERISTICS							
C _{iss}	Input Capacitance	V _{GS} = 0			700		pF
C _{oss}	Output Capacitance	V _{DS} = –25V			200		
C _{rss}	Reverse Transfer Capacitance	f = 1MHz			40		
Q _g	Total Gate Charge	V _{GS} = –10V		8		31	nC
Q _{gs}	Gate – Source Charge	I _D = –6.5A		0.8		7.0	
Q _{gd}	Gate – Drain (“Miller”) Charge	V _{DS} = 0.5BV _{DSS}		5.0		17	
t _{d(on)}	Turn–On Delay Time	V _{DD} = –100V				50	ns
t _r	Rise Time	I _D = –6.5A				100	
t _{d(off)}	Turn–Off Delay Time	R _G = 7.5Ω				100	
t _f	Fall Time					80	
SOURCE – DRAIN DIODE CHARACTERISTICS							
I _S	Continuous Source Current					–6.5	A
I _{SM}	Pulse Source Current ²					–28	
V _{SD}	Diode Forward Voltage ¹	I _S = –6.5A	T _J = 25°C			–6.0	V
		V _{GS} = 0					
t _{rr}	Reverse Recovery Time ¹	I _F = –6.5A	T _J = 25°C			400	ns
Q _{rr}	Reverse Recovery Charge	d _i / d _t ≤ –100A/μs	V _{DD} ≤ –50V			4	μC
t _{on}	Forward Turn–On Time			Negligible			
PACKAGE CHARACTERISTICS							
L _D	Internal Drain Inductance (measured from 6mm down drain lead to centre of die)				5.0		nH
L _S	Internal Source Inductance (from 6mm down source lead to source bond pad)				13		
THERMAL CHARACTERISTICS							
R _{θJC}	Thermal Resistance Junction – Case					1.67	°C/W
R _{θCS}	Thermal Resistance Case – Sink				0.12		
R _{θJA}	Thermal Resistance Junction – Ambient					30	

Notes

1) Pulse Test: Pulse Width $\leq 300\text{ms}$, $\delta \leq 2\%$

2) Repetitive Rating – Pulse width limited by maximum junction temperature.